**Features**

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable rectifiers

Part No. Y50ZPD-ZT50cT

I_{F(AV)}	1980A	
V_{RRM}	2200V	2500V
	2800V	3000V

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Double side cooled, T _C =85°C	160			1980	A
V _{RRM}	Repetitive peak reverse voltage	tp=10ms	160	2100		3000	V
I _{RRM}	Repetitive peak current	At V _{RRM}	160			80	mA
I _{FSM}	Surge forward current	10ms half sine wave	160			27	kA
I ² t	I ² t for fusing coordination	V _R =0.6V _{RRM}				3645	A ² s*10 ³
V _{FO}	Threshold voltage		160			0.82	V
r _F	Forward slope resistance					0.22	mΩ
V _{FM}	Peak forward voltage	I _{FM} =3000A, F=24kN	25			2.00	V
Q _{rr}	Recovery charge	I _{FM} =1000A, tp=4000μs, di/dt=-20A/μs, V _R =100V	160		3500		μC
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine: double side cooled Clamping force 24kN				0.020	°C /W
R _{th(c-h)}	Thermal resistance case to heat sink					0.005	
F _m	Mounting force			19		26	kN
T _{vj}	Junction temperature			-40		160	°C
T _{stg}	Stored temperature			-40		160	°C
W _t	Weight				440		g
Outline	ZT50cT						

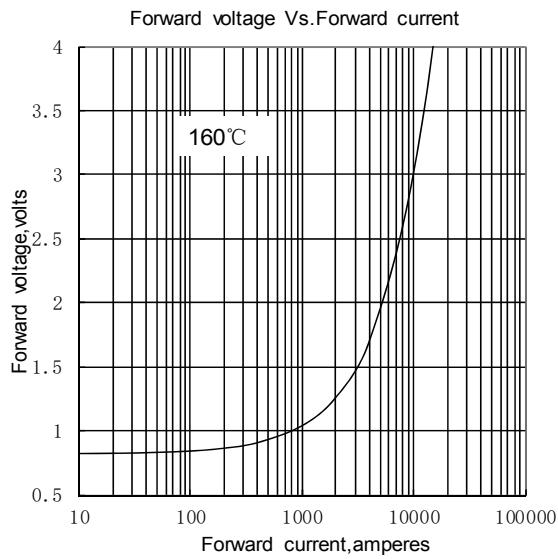


Fig.1

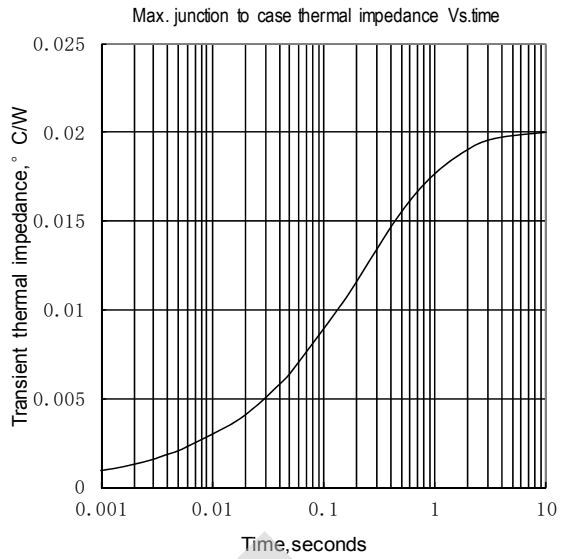


Fig.2

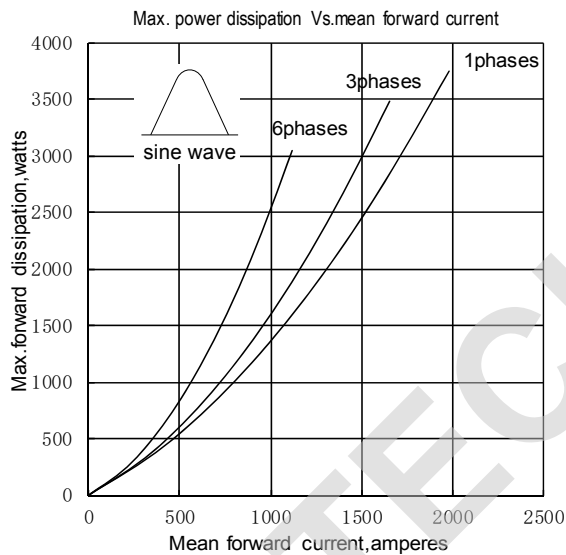


Fig.3

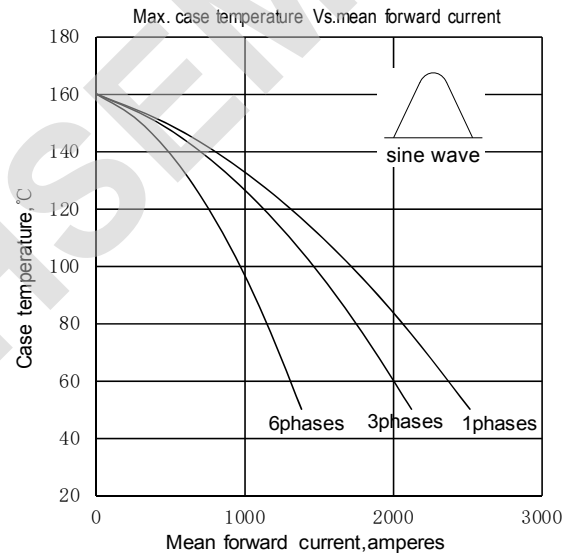


Fig.4

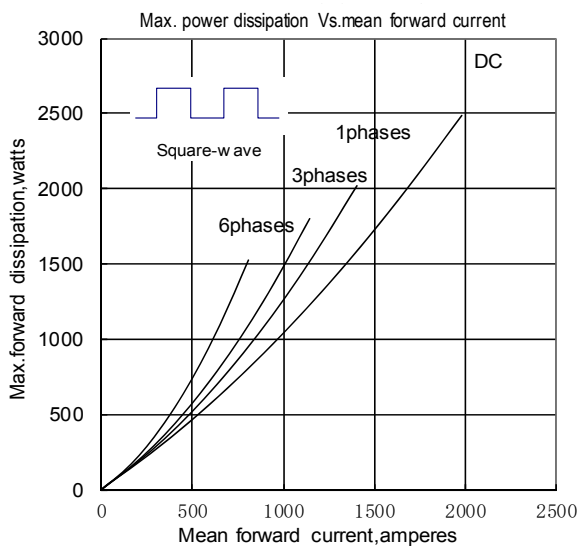


Fig.5

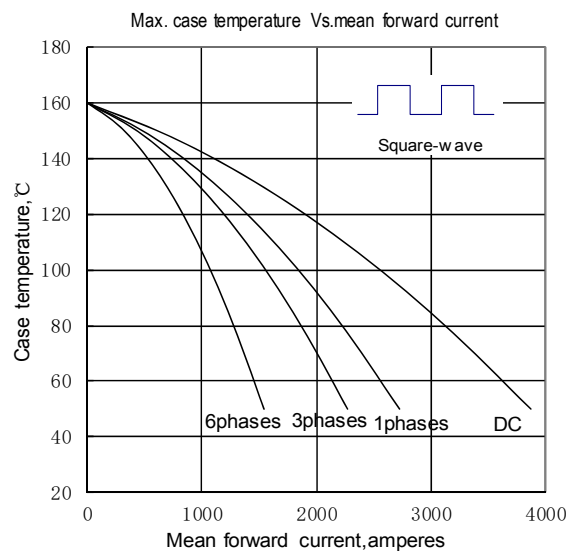


Fig.6

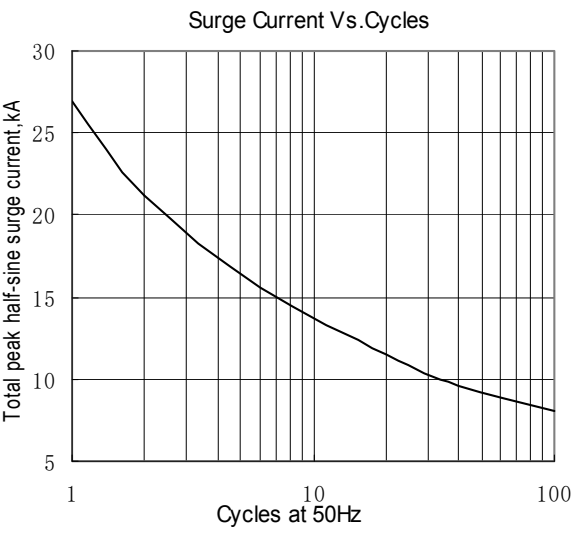


Fig.7

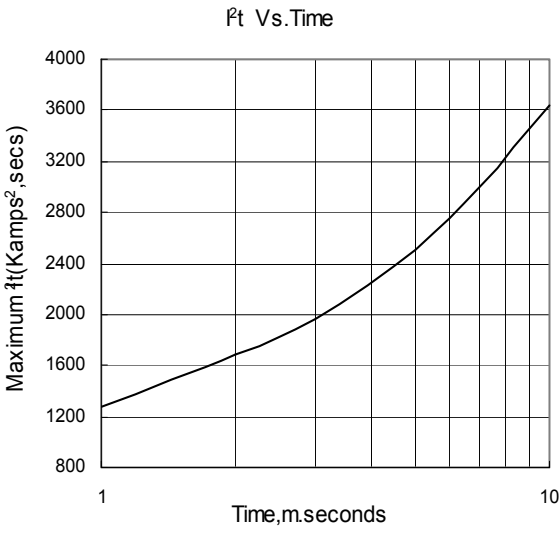
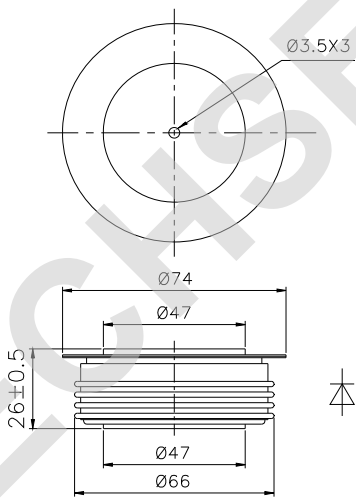


Fig.8

Outline:



TECHSEM reserves the right to change specifications without notice.